Electrical & Thermal Test Report

High Frequency Terminations Electrical and Thermal Test Report

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1. Scope

The purpose of this test report is to present the electrical and thermal performance of high frequency terminations developed under the project DD-217491. The report will show test data collected during the tests performed on these products. Both the pre-test simulation analysis as well as the tests on real prototypes will be displayed and analyzed. For a successful evaluation of the products at high frequencies, it is of a paramount importance for the products to be mounted on the test fixture using clearly defined mounting instructions. This report contains these mounting instructions for a future reference to be used by both the internal and external users. In addition, the test procedure is included with the test equipment used and best testing practices implemented.

Electrical performance has been evaluated through the simulation analysis and a real-life test of the DUTs in a test fixture on the vector network analyzer. Thermal performance has also been presented through a simulation and a real-life test. Thermal finite element analysis (FEA) simulations are carried out to calculate the maximum power handling of the family of parts in different environments (with different mounting constituents). The power test has been conducted in a destruct fixture that was described in the report. Finally, the set of samples has been exposed to a rigorous qualification that included Group A, Group B and Group C tests as per test plan TP-9270.

The test samples passed all the qualification test requirements. The test results that will be presented in this test report are an evidence of a successful test and viability of the products to be released into customers' applications.

2. Specifications

To cover the frequency bands of interest, two RF terminations have been developed with the part numbers CT0404ALN1WB1 and CT0404ALN2WB1. The size of both RF terminations is 0.040"×0.040"×0.015". These products were made using a thin-film based processes on an Aluminum Nitride ceramic substrate. Detailed specifications for these two products are shown in Tables and Figures below.

CT0404ALN1WB1						
ITEM	PARAMETER	REQUIREMENT	LIMITS	UNITS		
1	Nominal Impedance	$50\pm10\%$	-	Ω		
2	Frequency Range	DC – 42.5	-	GHz		
3	VSWR	1.60:1	maximum*	-		
4	Input Power	5.0	minimum	Watts		
5	Operating Temperature	-55 to +150	-	°C		
6	Non-Operating temperature	-65 to +150	-	°C		

Table 1 – Electrical and Non-Electrical Requirements for CT0404ALN1WB1

CT0404ALN2WB1						
ITEM	PARAMETER	REQUIREMENT	LIMITS	UNITS		
1	Nominal Impedance	$50\pm10\%$	-	Ω		
2	Frequency Range	DC – 64	-	GHz		
3	VSWR	1.60:1	maximum*	-		
4	Input Power	1	minimum	Watts		
5	Operating Temperature	-55 to +150	-	°C		
6	Non-Operating temperature	-65 to +150	-	°C		

Table 2 – Electrical and Non-Electrical Requirements for CT0404ALN2WB1

*VSWR relaxed from 1.60:1 maximum (from the spec indicated on the datasheets) to take into account the impact of the mismatch created by the test connectors.



Figure 1 - Power Derating at Temperature



Figure 2. 2D Drawing for CT0404ALN1WB1 and CT0404ALN2WB1 - Mechanical Footprint

3. Test Preparation - Electrical (RF) Simulations

Both part numbers have been simulated in multiple 2.5D or 3D electromagnetic simulators including Ansys HFSS, Dessault CST, National Instruments AWR, and Sonnet. The purpose of the modeling in various simulation tools is to compare the simulated performance and to establish the level of correlation between the simulation and the test.

After the designs have been optimized for a nominal performance, the tolerance analysis has been conducted that considered substrate thickness and dielectric constant variations, transmission line dimensional tolerances, and variations in the bulk resistivity and shape of the resistors.

Figure 3 shows the baseline model of CT0404ALN1WB1 design in Ansys HFSS, both as a stand-alone part as well as mounted and interfacing the test fixture.



Figure 3. Electrical Models of CT0404ALN1WB1: (a) stand-alone, (b) interfacing the fixture

Finally, the impact of the test fixture has also been evaluated in order to establish the baseline directions for the mounting of the DUT into the test fixture. Various scenarios have been analyzed to evaluate the impact of the interface between the termination and the application board (Figure 4). Both the ribbon bond and the wire bond have been taken into consideration. The cases that were of special interest in this tolerance analysis were the ribbon bond width and height, the number and size of the wire bonds, the thickness of the application board, and the air gap between the termination and the application board. As expected at these frequencies, the interface plays a crucial role in the performance of the termination and if not tuned properly, it may introduce significant undesired reflections (Figure 5).



Figure 4. Various tolerance scenarios: (a) ribbon bond (b) ribbon bond and air gap, (c) three wire bonds with significant height, (d) low height wire bonds, (e) thin application board

The simulation results show that the optimal performance would occur for <u>no gap between the</u> <u>application board and the termination</u> while ribbon (or wire bond) must spread over <u>the entire width</u> <u>of the trace</u> underneath. The application board must be positioned so that its <u>top surface plane is at</u> <u>the same level</u> as the top surface plane of the termination.



Figure 5. Simulated electrical performance for the scenarios shown in Fig 4 (a) – (e)

4. Test Fixture Choice

In order to properly fixture the presented RF termination and similar high frequency surface mount components for RF performance verification testing, the information about the medium (substrate) onto which the device will be mounted on during its intended field operation is needed. This is achieved by spending effort in first constructing a 'good' 50 Ω transmission through line with the line width sized to match the width of the DUT. The properties of PCB substrate such as dielectric constant and thickness are chosen to yield a transmission line that closely matches the DUT I/O pad widths. To reduce radiation losses, most of the test boards are realized in a grounded coplanar waveguide (CPWG) structure that exhibits better performance than the traditional microstrip line test fixtures at frequencies above 20 GHz. In addition to the argument above, CPWG lines also work very well with SMT (surface-mount) devices since the signal and ground are located on the same plane. The through line test fixture should be sized to match the final DUT test fixture size.





Figure 6. Test board used to interface the DUT with the connector

Essentially, the through line length will be the size of the input launch times two. The DUT test fixture length will be the through line length plus the DUT length for 2-port devices. A single port device, such as a termination fixture length will be that one launch length (half of the through line) plus the DUT length. The substrate thickness should be selected properly for the frequency of interest to avoid the creation of higher order modes that appear as undesired spikes on the display of the vector network analyzer (VNA). For the purpose of testing high frequency terminations CT0404ALN1WB1 and CT0404ALN2WB1, a test board made on Rogers 4350 substrate is utilized (Figure 6).

The test fixture will also include some sort of coaxial connector and a transition from planar board into the coaxial structure of the connector (Fig 4). The connector is chosen to support the operation frequency band and desired VSWR. For the purpose of testing high frequency terminations CT0404ALN1WB1 and CT0404ALN2WB1, we used Southwest Microwave field replaceable connectors:

- 2.4mm female (part #: 1492-03A-5) for CT0404ALN1WB1 (DC 42.5 GHz)
- 1.85 mm female (part #: 1892-04A-6) for CT0404ALN2WB1 (DC 64 GHz).

The 2.4 mm jack (female) end launch connector used for the tests at frequencies DC – 42.5 GHz is shown in Figure 7. It is important to mention that the selection of the connector pin (see dimensions ϕ A) on the connector (1.85mm or 2.4 mm) affects the connector launch performance and thus must be chosen as directed.



Figure 7. Southwest Microwave 2.4 mm connector used in tests at frequencies DC-42.5 GHz (drawing)

5. Mounting Instructions

First step in properly mounting the RF termination for testing is to carefully inspect all the components of the test fixture to be assembled. Special attention should be given to the test board edges (Figure 8a). Common PCB manufacturing often leave rough edges that can cause fixture assembly issues. The edges of the test board can usually be cleaned up using fine grit sand paper. (Figure 8b).



Figure 8. Test board transmission line: (a) rough edge (before cleaning), (b) smooth edge (after cleaning)

Next is the fixture assembly; the carrier board is soldered to the test board using Sn96 solder. Care should be taken to insure there is no solder run-out into the area where the DUT is to be mounted. The final step in the fixture assembly is to mount the connector to the test board. Things to look for at this step is to center the connector pin on the transmission line and to insure the connector is flush with the edge of the test board to avoid undesired air gaps (Figure 9). Use of a microscope is essential to insuring that the connector is mounted properly.



Figure 9. Connector pin alignment on the test board

Having a properly assembled test fixture, it is time to mount the RF termination. The RF termination should also be inspected to insure the edges are cleanly cut and have no jagged edges prior to being installed on the test fixture. Due to possible power handling requirements, the RF termination needs to be soldered in place. This presents challenges in proper alignment to the transmission line. When soldering, the termination tends to move during solder reflow. To prevent this, pure indium solder could be used. The indium solder is very soft, and the termination can be pressed into the solder before reflow.

which allows for fine adjustment of the termination to the transmission line and to ensure the termination is flush with the test board. When the termination is reflowed, it remains in place. Finally, the termination needs to be connected to the transmission line. There are primarily two types of connection methods, ribbon and wire bonding. Short ribbon bonds provide the best RF performance, but wire bonding is the most popular. In order to analyze the effects of the different connection methods, it is important to use the same termination. This can prove difficult as removing the ribbon or wire bonds can often damage the circuit. In order to prevent any damage, the ribbon bond can be replaced with a small piece of indium solder. The indium solder does not need to be reflowed but just pressed into place. The pliability of the indium allows for good contact to the transmission line and the termination. It can then be easily removed and replaced with the wire bonds. This allows for a direct comparison of the effects of the different connection methods using the identical termination and fixture. All good assembly practice start playing an extremely important role at high frequencies.



Figure 10. Bad mounting practices: (a) poor wire bond connection to the pad, (b) air gap between the termination and the application board, (c) poor wire bond, (d) wire bond sticking out of the pad area

As the simulation analysis showed, a small tolerances or changes in the shape and position of wire bonds, for example, can result in significant deterioration of electrical performance at high frequencies. Bad wire bond and other mounting practices (Figure 10) result in significant reflections that "mask" the true performance of the DUT. On the other side, proper installation (Figure 11) results in a good correlation between the designer's simulation and the tested prototype.



Figure 11. Close up of a properly installed RF termination on the test fixture; good correlation between the simulated model and the prototype

The mounting instructions are shown on the block diagram (Figure 12). The fully assembled test fixture (Figure 13) consists of the small grounded carrier (3) soldered to the back side of the test board (2) with the RF termination (4) installed using proper mounting practices described above. The Southwest microwave connector (1) is seen on the right side of the fixture.



Figure 12. The Mounting instructions – Flow Chart



Figure 13. Fully assembled test fixture used in the electrical test of high frequency terminations: 1 - connector*,* 2 - test board*,* 3 - ground carrier*,* 4 - DUT *(RF termination)*

6. **RF Test Results**

Typical performance of CT0404ALN1WB1 is shown in Figure 14. Both gated (termination only), and nongated (termination and connector), and time-domain data is shown. The prototypes exhibit a very repetitive VSWR performance under 1.30:1 for the entire frequency band DC-42.5 GHz.



Figure 14. Typical RF performance of CT0404ALN1WB1 termination: gated data (left), ungated data (bottom right, time-domain (top right)

Typical performance of CT0404ALN2WB1 is shown in Figure 15. Both gated (termination only), nongated (termination and connector) data, and time domain data is shown. The prototypes exhibit a very repetitive VSWR performance under 1.30:1 for the entire frequency band DC-64 GHz.



SAMPLE 1

Figure 15. Typical RF performance of CT0404ALN2WB1 termination: ungated data (top left), gated data (right), time domain data (bottom left)

7. Thermal (FEA) Simulation

Thermal FEA simulation has been performed on both RF terminations. Two types of thermal analysis are conducted - with input power at DC using SolidWorks and with input power at RF frequencies using CST MPHYSICS® STUDIO.

CST MPHYSICS® STUDIO (CST MPS) is a powerful and easy-to-use tool for thermal and mechanical stress analysis. High-frequency fields, currents and particle collisions are all sources of heat that EM engineers frequently encounter, and so CST MPS is fully integrated into CST STUDIO SUITE® to enable coupled EM-multiphysics simulation with other tools such as CST MICROWAVE STUDIO®, CST EM

STUDIO® and CST PARTICLE STUDIO®. With the CST MPS thermal solver, the changes in temperature generated by these interactions are modeled, and heat flow within the device simulated to test the performance of heat sinks and ensure the reliability of temperature-sensitive components. From the temperature distribution, CST MPS® can also calculate the thermal expansion of the components and the stress and strain within it as it presses against its housing, using the mechanical solver. The results of the thermal expansion simulation can even be fed back into the EM simulations, offering the opportunity to perform a sensitivity analysis of the device's response to heating.

For both the simulation in SolidWorks and the simulation in CST MPHYSICS® STUDIO, the baseplate temperature used in the simulation was 100°C. This boundary condition was assigned to the bottom of the RF termination. All losses including losses in dielectrics and conductors were taken into account; losses from RF simulation were exported into the thermal modeler and used to properly simulate thermal flow through the structure. The film temperature of 150°C is chosen as a conservative design point to avoid resistance drift due to thermal coefficient of resistivity. Significantly higher film temperature can lead to a drift in resistance and change in attenuation. Good correlation has been established between the two types of simulation. The simulations showed that CT0404ALN1WB1 can handle 8 W of power (which is a significant margin of about 3W relative to the specification of 5W) while CT0404ALN2WB1 can handle around 4 W of input power (which is a significant margin compared to the specification of 0.5 W nominal).



Figure 16. Simulated thermal performance of CT0404ALN1WB1 in SolidWorks (left) and CST MPHYSICS® *Studio (right)*



Figure 17. Simulated thermal performance of CT0404ALN2WB1 in SolidWorks (left) and CST MPHYSICS® *Studio (right)*

As a next step, the impact of different types of heat sinks on the thermal performance of the RF terminations has been analyzed through SolidWorks software. The first set of simulations assumes an ideal infinite heatsink with a perfect bond. The bottom of the ceramic substrate is kept at a 100° C isothermal boundary condition. The results of this simulation show the chip power rating.

The next set of simulations assumes an ideal infinite heatsink with a silver epoxy bond. The bottom of the silver epoxy is kept at a 100°C isothermal boundary condition. The silver epoxy is Loctite Ablebond 8700 E with a bond line thickness of 0.001" and 0.002" and thermal conductivity of 1.6 W/mK. The results of this simulation show the power rating as mounted.

Thermal FEA Results: Ideal Infinite Heatsink with Perfect Bond		Thermal FEA Results: with 1 mil S	Ideal Infinite Heatsink Silver Epoxy	Thermal FEA Results: Ideal Infinite Heatsink with 2 mil Silver Epoxy	
PART	Power	PART	Power	PART	Power
NUMBER	(W)	NUMBER	(W)	NUMBER	(W)
CT0404ALN1WB1	8	CT0404ALN1WB1	3.02	CT0404ALN1WB1	1.88
CT0404ALN1WB2	4	CT0404ALN1WB2	2.16	CT0404ALN1WB2	1.53

Table 3 - Thermal FEA Results for different heatsink configurations



Figure 18. Plot of Power vs Thickness of Silver Epoxy

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The true power rating of the RF chip termination in the assembly will also depend on the real heatsink material for the chip mounting. There will be differences in power handling depending whether the material is a high thermal conductive metal or a poor thermal conductivity PCB material.



Figure 19. Thermal FEA Plots: Ideal Infinite Heatsink with Perfect Bond: CT0404ALN1WB1 (left), CT0404ALN2WB1 (right)



Figure 20. Thermal FEA Plots: Ideal Infinite Heatsink with 1 mil thick Silver Epoxy: CT0404ALN1WB1 (left), CT0404ALN2WB1 (right)



Figure 21.Thermal FEA Plots: Ideal Infinite Heatsink with 2 mil thick Silver Epoxy. CT0404ALN1WB1 (left), CT0404ALN2WB1 (right)

8. Power Test

The RF termination (DUT) has been soldered mounted onto a copper flange using Indium solder. The flange has then been bolted onto the copper heat sink with a chiller. A thin layer of thermal compound (arctic silver) has been applied between the flange and the heat sink to provide for better thermal transfer (Figure 22). The DUT has been exposed to incremental DC power levels by adjusting the voltage on the DC sources connected to the test fixture through the wire as shown in Figure 22. The baseplate temperature (boundary condition) has been kept at 100°C and the resistance value on the film monitored for any significant changes. The table 4 shows the collected results; the termination has been exposed to 15 W max with no significant performance reduction. No mechanical changes have been observed through the visual inspection of the DUT after the test was performed.



Figure 22. Test fixture used for the power handling test of the high frequency terminations

40 GHz Termination								
	Initial 4-wire resistance = 50.11Ω							
Date	Time		Volts	Amps	Ohms	Watts		
6/10/2019	14:15		15.83	0.322	49.16149	5.09726		
	16:00		15.83	0.321	49.31464	5.08143		
6/11/2019	8:00		15.83	0.321	49.31464	5.08143		
	8:35		20.09	0.41	49	8.2369		
	10:00		20.09	0.4098	49.02391	8.232882		
	13:00		20.09	0.4097	49.03588	8.230873		
	17:10		20.09	0.4097	49.03588	8.230873		
6/12/2019	8:00		20.09	0.4097	49.03588	8.230873		
	10:30		20.09	0.4097	49.03588	8.230873		
	10:35		22.37	0.4575	48.89617	10.23428		
	11:00		22.37	0.4574	48.90686	10.23204		
	16:15		22.37	0.4574	48.90686	10.23204		
	16:20		27.419	0.5648	48.54639	15.48625		
6/13/2019	8:00		27.419	0.5641	48.60663	15.46706		
	10:15		27.419	0.5641	48.60663	15.46706		
6/14/2019	8:00		27.42	0.5639	48.62564	15.46214		
	10:30		27.417	0.5639	48.62032	15.46045		

Table 4 – DC power test of CT0404ALN1WB1 termination (results)

9. Qualification Test

The purpose of this test is to subject the high frequency terminations to the conditions as specified in the test plan TP-9270 and qualify them internally for the markets to be served. The CT0404ALN1WB1 42.5GHz termination will be subjected to the tests while the termination CT0404ALN2WB1 64.0GHz will be qualified by similarity. The Specification Control Drawing (SCD, see Tables 1 and 2) of the device is the governing document for all specification limits for each test, with any exceptions noted herein. Qualification testing references MIL-PRF-55342, for Class L devices, with the exceptions noted in this document.

Devices were mounted on destruct fixturing in order to facilitate performance of the required tests. Removable RF connectors were mounted only when RF test is called out. Test frequencies are defined as 'low' = 1GHz, 'mid' = (maxfreq-1GHz)/2 = 20.5 GHz, rounded to the nearest 2-decimal places, & 'high' = 42 GHz per SCD. Devices with damaged wire bonds were re-wire bonded.

Change in resistance incurred by tests performed was noted (if any) and used for the specification risk assessment and the final device rating. All electrical tests were conducted at DC as power handling is the main concern for the qualification. RF performance was verified at the end of each test group.



Figure 23. Flowchart of Test Procedure

GROUP A INSPECTION (100% of the lot, 25 samples and 3 extra test setup pieces)

Each inspection lot was subjected to 100% Group A inspection. The inspection lot devices were mounted onto a PCB/test fixture prior to Electrical Inspection.

Visual Mechanical Inspection Results

The materials, design, construction, physical dimensions, markings and workmanship were verified to be in accordance with applicable requirements per the appropriate SCD.



Figure 24. Group A inspection lot: test fixtures without the connectors installed (left), test fixture with the connectors installed (right)

Initial Electrical (INI) Test Results

DC resistance between the input port and the ground path (Figure 25) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits were as per the SCD. VSWR (or Return Loss) has then been measured and recorded at low, mid and high frequencies on a Vector Network Analyzer (VNA), in accordance with MIL-STD-39030, Method 4.6.10. S-parameter file for each device has been captured. Acceptance limits were as per the SCD. As indicated in Table 5, the inspection lot passed the required specification as per SCD.





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HF Series Terminations	per Test Plan TP-9270			
Test Group	Δ.	Part Number	CT040	4ALN1\W/R1
Test Sequence	Δ2	Description	42GHz HE Termin	ation Wire bondable
Test Sequence	Initial Electrical (DC & BE)	Description	42011211111111	
Test Step		Revision		-
Quantity	28	Test Plan	Т	P-9270
Date In	8/28/2019	Factory Order	RE	F 4759
Date Out	8/30/2019	Lot Code	RE	F 4759
Operator	JA	Results		Pass
· ·				
Nominal Resistance Value	50	Ω		
Upper Limit DCR	55	Ω	1	
Lower Limit DCR	45	Ω		
VSWR Limit	1.36	:1		
		Initial M	leasurements	
Serial Number	DC Resistance (Ω)	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz
1	47.23	1.04	1.30	1.18
2	50.26	1.04	1.30	1.23
3	47.08	1.04	1.32	1.19
4	47.02	1.04	1.33	1.15
5	50.03	1.05	1.30	1.14
6	47.70	1.03	1.33	1.18
7	47.73	1.03	1.31	1.16
8	47.60	1.03	1.31	1.15
9	47.39	1.04	1.30	1.16
10	47.23	1.04	1.33	1.17
11	51.20	1.06	1.24	1.14
12	50.62	1.04	1.25	1.17
13	50.57	1.06	1.26	1.19
14	47.57	1.03	1.30	1.16
15	47.57	1.03	1.29	1.15
16	48.57	1.02	1.30	1.16
17	48.09	1.03	1.29	1.16
18	48.19	1.03	1.32	1.20
19	48.29	1.03	1.36	1.18
20	48.44	1.03	1.31	1.18
21	48.09	1.03	1.32	1.22
22	48.35	1.02	1.32	1.19
23	47.49	1.03	1.35	1.22
24	48.21	1.03	1.31	1.18
25	48.62	1.02	1.35	1.17
26	51.37	1.06	1.26	1.20
27	47.15	1.03	1.31	1.16
28	52.71	1.10	1.22	1.23

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Table 5. Group A Initial Electrical Test Results - Summary

Figure 26. Group A Initial Electrical Test Results – RF performance of a typical sample from the inspection lot

Thermal Shock

The inspection lot samples were exposed to 10 cycles of thermal shock, -55°C to +125°C in accordance with MIL-STD-202, Method 107 (see Table 6). The equipment used for the test consisted of Thermotron, model ATS-30-4-4 with the asset tag # TE90075.

STEP	TEMPERATURE (°C)	TIME (MINUTES)
1	-55 (+0/-3)	15 min.
2	+25 (+10/-5)	5.0 max.
3	+125 (+3/-0)	15 min.
4	+25 (+10/-5)	5.0 max.

Table 6. Thermal Shock temperature levels and exposure times

After Thermal Shock Electrical (ATS) Test Results

DC resistance between the input port and the ground path (Figure 25) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits were as per the SCD and DCR $\Delta \pm 0.5$ % from initial electrical. As indicated in Table 7, the inspection lot samples passed the requirements.

HF Series Terminations p	per Test Plan TP-9270	niths interview of the second	rconnect	
Test Group	А	Part Number	CT0404/	ALN1WB1
Test Sequence	A4	Description	42GHz HF Termina	tion, Wire bondable
Test Step	Post Thermal Shock Electrical (DC) Inspection	Revision		-
Quantity	28	Test Plan	TP-	9270
Date In	9/6/2019	Factory Order	REF	4759
Date Out	9/6/2019	Lot Code	REF	4759
Operator	JA	Results	Pa	ass
Nominal Resistance Value	50	Ω		
Upper Limit DCR	55	Ω		
Lower Limit DCR	45	Ω		
Delta DCR	0.50	% (±)		
	After Therm	nal Shock	Initial	
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)	
1	47.23	0.00	47.23	
2	50.26	0.00	50.26	
3	47.08	0.00	47.08	
4	47.00	-0.04	47.02	
5	50.03	0.00	50.03	
6	47.70	0.00	47.70	
7	47.73	-0.01	47.73	
8	47.61	0.03	47.60	
9	47.39	0.00	47.39	
10	47.24	0.01	47.23	
11	51.21	0.02	51.20	
12	50.63	0.02	50.62	
13	50.57	0.00	50.57	
14	47.55	-0.05	47.57	
15	47.57	0.01	47.57	
16	48.58	0.02	48.57	
17	48.10	0.02	48.09	
18	48.19	0.01	48.19	
19	48.30	0.01	48.29	
20	48.44	0.01	48.44	
21	48.10	0.01	48.09	
22	48.36	0.02	48.35	
23	47.49	0.01	47.49	
24	48.22	0.01	48.21	
25	48.02	0.00	48.02	
20	51.3/	-0.01	51.3/	
2/	47.15	0.01	47.15	
۷۵	52.72	0.02	52.71	

Table 7. Group A Post Thermal Shock Electrical Inspection Results

Bake (100% de-rated burn-in):

The devices were subjected to a 168 hour bake (100% de-rated burn-in) at 150°C. The equipment used in the test – Fischer Scientific isotemp oven with an asset tag # TE91660 and Omega HH502 thermometer with an asset tag TE40080. The entire lot was placed in the appropriate burn in fixture for the product family (Figure 27). The fixture was placed in the appropriate temperature controlled preheated chamber. The power was turned on and 168-hour test started. The temperature was monitored periodically to ensure test is not disrupted. After 168 hours had been concluded, the parts were removed from the chamber and stabilized at the room temperature until tray was cool (1 hour min).



Figure 27. Burn-in fixture for the bake test

After Burn-in Electrical Test Results

DC resistance between the input port and the ground path (Figure 25) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits were as per the SCD and DCR $\Delta \pm 0.5$ % from after the thermal shock electrical.

VSWR (or Return Loss) has then been measured and recorded at low, mid and high frequencies on a Vector Network Analyzer (VNA), in accordance with MIL-STD-39030, Method 4.6.10. S-parameter file for each device has been captured. Acceptance limits were as per the SCD.

As shown in Table 8, the inspection lot samples passed the requirements.

HF Series Terminations	per Test Plan TP-9270			Smit bringing ter	hs interc	onnect
Test Group	A	Part Number	CT0404A	LN1WB1		
Test Sequence	A6	Description	42GHz HF Terminat	ion, Wire bondable		
Test Step	Post Burn In Electrical (DC & RF) Inspection	Revision	-	-		
Quantity	28	Test Plan	TP-9	9270		
Date In	9/17/2019	Factory Order	REF	4759		
Date Out	9/19/2019	Lot Code	REF	4759		
Operator	JA	Results	Pa	ISS		
Nominal Resistance Value	50	Ω				
Upper Limit DCR	55	Ω				
Lower Limit DCR	45	Ω				
Delta DCR	0.50	% (±)				
VSWR Limit	1.36	:1				
	After Bu	irn-In	After Thermal Shock			
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz
1	47.23	0.00	47.23	1.03	1.30	1.16
2	50.26	0.02	50.26	1.07	1.29	1.19
3	47.08	0.00	47.08	1.03	1.30	1.15
4	47.01	0.01	47.00	1.03	1.31	1.13
5	50.03	0.01	50.03	1.06	1.27	1.13
6	47.71	0.01	47.70	1.03	1.32	1.16
7	47.73	0.00	47.73	1.03	1.30	1.14
8	47.61	0.01	47.61	1.03	1.29	1.13
9	47.40	0.01	47.39	1.03	1.29	1.14
10	47.24	0.00	47.24	1.03	1.31	1.13
11	51.22	0.02	51.21	1.07	1.22	1.12
12	50.63	0.00	50.63	1.00	1.24	1.14
13	30.38	0.02	30.37	1.07	1.25	1.10
14	47.55	0.01	47.55	1.03	1.29	1.15
15	47.50	0.01	47.57	1.03	1.27	1.12
10	48.33	0.01	48.38	1.03	1.30	1.18
18	48.10	0.00	48.10	1.03	1.25	1.14
19	48.20	0.01	48.15	1.05	1.31	1.15
20	48.45	0.01	48.30	1.04	1.34	1.15
20	48.11	0.02	48.10	1.04	1 31	1.15
22	48.36	0.01	48.36	1.03	1.30	1.16
23	47.50	0.01	47.49	1.03	1.34	1.19
24	48.22	0.01	48.22	1.04	1.30	1.14
25	48.63	0.01	48.62	1.04	1.34	1.17
26	51.38	0.02	51.37	1.08	1.25	1.17
27	47.16	0.01	47.15	1.03	1.30	1.12
28	52.74	0.02	52.72	1.12	1.21	1.18

Table 8. Group A Post Burn In Electrical Test Results - Summary



Figure 28. Group A Post Burn In Electrical Test Results – RF performance of a typical sample from the inspection lot

Percent Defective Allowable (PDA) Analysis Results

Percentage Defective Allowable (PDA) Analysis was performed on the Group A inspection lot. The defective percentage was calculated to be 0% which is below an acceptable 10%. It was concluded that the inspection lot that was subjected to the test passed the Group A testing and could be moved over to the Group B test stage.

GROUP B INSPECTION (10 samples):

Ten (10) samples from the Group A inspection lot were randomly selected. The 10-sample lot was divided into three subgroups – subgroup 1 (quantity 3), subgroup 2 (quantity 4), and subgroup 3 (quantity 3).

SUBGROUP 1 (3pc sample) TEST RESULTS

Resistance to Temperature Characteristics

Devices were tested in accordance with MIL-STD-202, Method 304. The test was performed according to the following details and exceptions:

- Reference temperature: room ambient temperature.
- Test temperatures:
 - Step 1: room temperature.
 - Step 2: -55°C.
 - Step 3: room temperature.
 - Step 4: +125°C.
- Accuracy of temperature measurement: Devices were maintained within 3°C of each test temperature for a period of 30 to 45 minutes. Acceptance limits: per the SCD.

The thermal chamber used is shown in Figure 29, the RF performance at three temperature levels presented in Figures 30-32, and the test summary in the Table 9. As shown in the test results below, the inspection lot samples passed the requirements.



Figure 29. Devices under test in the thermal chamber



Figure 30. Typical RF performance of the Group B, subgroup 1 sample at Room (+25°C) Temperature: gated data (left), ungated data (bottom right), time domain (top right)



Figure 31. Typical RF performance of the Group B, subgroup 1 sample at Cold (-55°C) Temperature: gated data (left), ungated data (bottom right), time domain (top right)



Figure 32. Typical RF performance of the Group B, subgroup 1 sample at Hot (+125°C) Temperature: gated data (left), ungated data (bottom right), time domain (top right)

HF Series Terminations	per Test Plan TP-9270			
Test Group	В	Part Number	CT0404A	LN1WB1
Test Sequence	B1-1	Description	42GHz HF Terminat	ion, Wire bondable
Test Step	Resistance to Temperature Characteristics	Revision		
Quantity	3	Test Plan	TP-9	270
Date In	10/16/2019	Factory Order	REF 4	4759
Date Out	10/17/2019	Lot Code	REF 4	4759
Operator	JA	Results	Pa	SS
Nominal Resistance Value	50	Ω		
Upper Limit DCR	55	Ω		
Lower Limit DCR	45	Ω		
Delta DCR	200	ppm/°C (±)		
VSWR Limit	1.40	:1		
Note: * Device SN 11 tested at	RF & max gated VSWR rep	orted, in lieu of DCR. RT	C not calculated.	
	25C	-55C	RTC Cold	
Serial Number	DC Resistance (Ω)	DC Resistance (Ω)	∆ DC Resistance (ppm)	
9	47.35	47.81	12.20	
12	50.60	51.10	12.48	
	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz	
11*	1.08	1.23	1.16	
	25C	+125C	RTC Hot	
Serial Number	DC Resistance (Ω)	DC Resistance (Ω)	Δ DC Resistance (ppm)	
9	47.35	46.79	-11.87	
10	50.60	49.98	-12.19	
	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz	
11*	1.06	1.22	1.12	
	25C Return			
Serial Number	DC Resistance (Ω)			
9	47.55			
10	47.60			
	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz	
11*	1.07	1.22	1.13	

Table 9. Group B, Subgroup 1 Test over Temperature Results - Summary

SUBGROUP 2 (4pc sample) TEST RESULTS

Initial Electrical (INI)

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DC resistance between the input port and the ground path (Figure 25) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits were as per the SCD plus DC resistance $\Delta \pm 0.5$ % from the previous electrical test. As shown in Table 10, the 4-sample inspection lot passed the requirements.

HF Series Terminations per Test Plan TP-9270							
Test Group	В	Part Number	CT0404A	ALN1WB1			
Test Sequence	B2-2	Description	42GHz HF Terminat	ion, Wire bondable			
Test Step	Low Temperature Operation	Revision		-			
Quantity	4	Test Plan	TP-9	9272			
Date In	10/1/2019	Factory Order	REF 4	4759			
Date Out	10/1/2019	Lot Code	REF 4	4759			
Operator	JA	Results	Pass				
Nominal Resistance Value	50	Ω					
Upper Limit DCR	55	Ω					
Lower Limit DCR	45	Ω					
Delta DCR	0.50	% (±)					
Power Handling	5	W					
	After Low 1	Temp Op	Initial				
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)				
5	50.04	0.01	50.03				
6	47.74	0.06	47.71				
7	47.75	0.03	47.73				
8	47.62	0.03	47.61				

Table 10. Group B, Subgroup 2 Initial Electrical Results - Summary

Low Temperature Operation Test Results

After the devices were mounted to the heatsink and allowed to stabilize at -55°C +0°/-5°C for one hour, the full rated DV voltage was applied for a duration of 45 minutes as per MIL-PRF-55342, Par 4.8.5. The DC resistance path was measured before and after the stabilization at 25°C and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits: per the SCD plus DC resistance $\Delta \pm 0.25$ % from the previous electrical test.

Peak Power Test Results

The devices were mounted on a suitable heatsink and subjected to peak power with the following characteristics DC pulse characteristics: 10 ms pulse duration and 1% duty cycle (1millisecond period) at ten times (10X) the maximum continuous power of 5 W, as per MIL-DTL-3933, Par 4.7.11.7. Devices were mounted on a suitable heatsink (see Figure 33).



Figure 33. Peak Power Test Setup

DC resistance between the input port and the ground path (Figure 25) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits as per the SCD plus DC resistance $\Delta \pm 0.5$ % from the previous electrical test. As shown in Table 11, the 4-sample inspection lot passed the requirements.

HF Series Terminations	s per Test Plan TP-9270			
Test Group	В	Part Number	CT0404A	LN1WB1
Test Sequence	B2-4	Description	42GHz HF Termina	tion, Wire bondable
Test Step	Peak Power Test	Revision		-
Quantity	4	Test Plan	TP-9	9272
Date In	10/1/2019	Factory Order	REF	4759
Date Out	10/1/2019	Lot Code	REF	4759
Operator	JA	Results	Pa	iss
Nominal Resistance Value	50	Ω		
Upper Limit DCR	55	Ω		
Lower Limit DCR	45	Ω		
Delta DCR	0.50	% (±)		
Power Handling	5	W		
	After Peak P	ower Test	Initial (ALTO)	
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)	
5	50.05	0.02	50.04	
6	47.73	-0.01	47.74	
7	47.75	0.02	47.75	
8	47.62	0.00	47.62	

Table 11. Group B, Subgroup 2 Post Peak Power Electrical Test Results - Summary

Power Conditioning Test Results

The devices were subjected to the maximum input power of 5 W (as specified in the SCD) by applying the equivalent DC voltage to properly mounted devices on a suitable heat sink alternating the power one and one-half hours "on" and one-half hour "off", for a total of 100 +48/-0 hours at 70°C maximum base temperature per MIL-PRF-55342, Par 4.8.4. Towards the completion of first "on" cycle, the base temperature was measured to ensure that it does not exceed maximum rated temperature.

DC resistance between the input port and the ground path (Figure 23) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits were as per the SCD plus DC resistance $\Delta \pm 0.5$ % from the previous electrical test. As shown in Table 12, the 4-sample inspection lot passed the requirements.

HF Series Termination	s per Test Plan TP-9270	Smi	technology to life	connect
Test Group	В	Part Number	CT0404A	LN1WB1
Test Sequence	B2-7	Description	42GHz HF Termina	tion, Wire bondable
Test Step	Power Conditioning	Revision		-
Quantity	25	Test Plan	TP-9	9272
Date In	10/1/2019	Factory Order	REF	4759
Date Out	10/7/2019	Lot Code	REF	4759
Operator	JA Results		Pass	
Nominal Resistance Value	50	Ω		
Upper Limit DCR	55	Ω		
Lower Limit DCR	45	Ω		
Delta DCR	0.50	% (±)		
Power Handling	5	W		
	After Power Conditioning		Initial (APP)	
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)	
5	50.07	0.05	50.05	
6	47.75	0.03	47.73	
7	47.77	0.04	47.75	
8	47.65	0.05	47.62	
7 8	47.75 47.77 47.65	0.03 0.04 0.05	47.73 47.75 47.62	

Table 12. Group B, Subgroup 2 Post Power Conditioning Electrical Test Results - Summary

High Temperature Exposure Test Results

The devices were subjected to $150^{\circ}C \pm 5^{\circ}C$ for a period of 100 hours ± 4 hours per MIL-PRF-55342, Method 4.8.7.

DC resistance between the input port and the ground path (Figure 25) was measured and recorded in accordance with MIL-STD-202, Method 303. Acceptance limits were as per the SCD plus DC resistance $\Delta \pm 0.5$ % from the previous electrical test. As shown in Table 13, the 4-sample inspection lot passed the requirements.

HF Series Terminations p	per Test Plan TP-9270			Smu bringing te	chnology to life	connect
Test Group	В	Part Number	CT0404A	LN1WB1		
Test Sequence	B2-10	Description	42GHz HF Terminat	ion, Wire bondable		
Test Step	High Temperature Exposure	Revision	-			
Quantity	4	Test Plan	TP-9270			
Date In	10/7/2019	Factory Order	REF 4759			
Date Out	10/14/2019	Lot Code	REF 4759			
Operator	JA	Results	Pass			
Nominal Resistance Value	50 Ω					
Upper Limit DCR	55 Ω					
Lower Limit DCR	45 Ω					
Delta DCR	0.50 % (±)					
VSWR Limit	1.36	:1				
	After High Temperature Exposure		Initial (APC)	VSWR (AHTE)		
Serial Number	DC Resistance (Ω)	∆ DC Resistance (%)	DC Resistance (Ω)	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz
5	50.08	0.01	50.07	1.03	1.26	1.17
6	47.75	0.00	47.75	1.02	1.31	1.17
7	47.77	0.00	47.77	1.03	1.30	1.13
8	47.65	0.01	47.65	1.03	1.31	1.14

Table 13. Group B, Subgroup 2 Post High Temperature Exposure Electrical Test Results - Summary

Final RF Test (RF FIN)

VSWR performance (or Return Loss [RL]) of the DUTs was measured and recorded at low, mid and high frequencies on a Vector Network Analyzer (VNA), in accordance with MIL-STD-39030, Method 4.6.10. S-parameter files are captured for each device. Acceptance limits were as per the SCD.

SUBGROUP 3 (3pc sample) TEST RESULTS

Wire Bond Integrity Test Results

A pull of 4 grams was applied by inserting a hook under the lead wire at approximately the center of the bond wire. The force was applied at a 90-degree angle to the surface of the chip, one lead per device for a minimum of 30 seconds per MIL-PRF-55342, Method 4.8.13.3. As indicated in Table 14, the subgroup 3 devices passed the test.

HF Series Terminations per Test Plan TP-9270 Smiths interconnect bringing technology to life				
Test Group	В	Part Number	CT0404ALN1WB1	
Test Sequence	B3-1	Description	42GHz HF Termination, Wire bondable	
Test Step	Wire Bond Pull Strength	Revision	-	
Quantity	3	Test Plan	TP-9272	
Date In	10/29/2019	Factory Order	REF 4759	
Date Out	10/29/2019	Lot Code	REF 4759	
Operator	ТР	Results	Pass	
Pull Strength	4	g		
Duration	30	secs.		
Serial Number	Non-destruct Bond Pull (g)	Destruct Bond Pull (g)		
10	Pass	6.1		
13	Pass	5.4		
14	Pass	7.6		

Table 14. Group B, Subgroup 3 Wire Bond Integrity Test Results - Summary

Solder Mounting Integrity Test Results:

Devices were soldered to a suitable substrate. A .75-kilogram force was applied to the chip edge for 30 seconds per MIL-PRF-55342, Method 4.8.13.1. The devices were then visually inspected for any evidence of mechanical damage. As indicated in Table 15, the subgroup 3 devices passed the test.

HF Series Termination	s per Test Plan TP-9270	smiths interconnect		
Test Group	В	Part Number	CT0404ALN1WB1	
Test Sequence	B3-2	Description	42GHz HF Termination, Wire bondable	
Test Step	Solder Mounting	Revision	-	
Quantity	3	Test Plan	TP-9272	
Date In	10/30/2019	Factory Order	REF 4759	
Date Out	10/30/2019	Lot Code	REF 4759	
Operator	TFM	Results	Pass	
Pull Strength	0.75	kg.		
Duration	30	secs.		
Serial Number	Solder Mounting Integrity			
10	Pass			
13	Pass			
14	Pass			

 \pm Table 15. Group B, Subgroup 3 Solder Mounting Integrity Test Results - Summary

GROUP C INSPECTION (4 samples):

Group C inspection was conducted on randomly selected samples that have been previously subjected to Group A Inspection.

Life Test (1000 hr Burn-In):

The devices were subjected to the maximum input power specified in the SCD by applying the equivalent DC voltage to properly mounted devices on a suitable heat sink for a total of 1000 +48/-0 hours at 70°C base temp. The power was continuously increased until the maximum power and base temp were achieved. Electrical (DC Resistance) measurements were made and recorded after 250 +48/-0, 500 +48/-0, and 1000 +48/-0 hours. Acceptance limits were as per the SCD plus DC Resistance Δ 0.5 % from after previous electrical test.

VSWR performance (or Return Loss) of the DUTs was measured and recorded at low, mid and high frequencies on a Vector Network Analyzer (VNA), in accordance with MIL-STD-39030, Method 4.6.10. S-parameter files are captured for each device. Acceptance limits as per the SCD.

HF Series Terminations	s per Test Plan TP-9270	smiths interconnect bringing technology to life			
Test Group	С	Part Number	CT0404/	ALN1WB1	
Test Sequence	C2	Description	42GHz HF Termination, Wire bondabl		
Test Step	Life Test	Revision		-	
Quantity	4	Test Plan	TP-	9272	
Date In	9/20/2019	Factory Order	REF	4759	
Date Out	11/1/2019	Lot Code	REF 4759		
Operator	JA	Results	Pass		
Nominal Resistance Value	50	Ω			
Upper Limit DCR	55	Ω			
Lower Limit DCR	45	Ω			
Delta DCR	0.50	% (±)			
Power Handling	5	W			
10/1/2019	After 250) Hours	Initial		
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)		
1	47.27	0.10	47.22		
2	50.31	0.12	50.25		
3	47.11	0.08	47.07		
4	47.03	0.03	47.01		
10/10/2019	After 470) Hours	250 Hours		
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)		
1	47.30	0.06	47.27		
2	50.34	0.06	50.31		
3	47.13	0.05	47.11		
4	47.05	0.05	47.03		
11/1/2019	After 1000) Hours	470 Hours		
Serial Number	DC Resistance (Ω)	∆ DC Resistance (%)	DC Resistance (Ω)		
1	47.28	-0.04	47.30		
2	50.32	-0.04	50.34		
3	47.12	-0.02	47.13		
4	47.04	-0.04	47.05		

Table 16. Group C After 1000 hour Life Test Electrical Results - Summary

HF Series Terminations per Test Plan TP-9270 smiths interconnect bringing technology to life						
Test Group	С	Part Number	CT0404A	LN1WB1		
Test Sequence	C3	Description	42GHz HF Termination, Wire bondable			
Test Step	Post Life Electrical (DC & RF) Inspection	Revision	-			
Quantity	4	Test Plan	TP-9270			
Date In	11/1/2019	Factory Order	REF 4759			
Date Out	11/4/2019	Lot Code	REF 4759			
Operator	JA	Results	Pass			
Nominal Resistance Value	50	Ω				
Upper Limit DCR	55	Ω				
Lower Limit DCR	45	Ω				
Delta DCR	0.50	% (±)				
VSWR Limit	1.36	:1				
	After 1000 hr Life Test		Life Test OHrs			
Serial Number	DC Resistance (Ω)	Δ DC Resistance (%)	DC Resistance (Ω)	VSWR @ 1 GHz	VSWR @ 20.5 GHz	VSWR @ 42 GHz
1	47.28	0.11	47.22	1.03	1.29	1.13
2	50.32	0.13	50.25	1.07	1.28	1.18
3	47.12	0.11	47.07	1.03	1.30	1.14
4	47.04	0.05	47.01	1.03	1.31	1.13



Table 17. Post Life Electrical Results - Summary

Figure 34. Typical RF performance of the Group C sample after the life test (1000 hr): gated data (left), ungated data (bottom right), time domain (top right)

10. Qualification Test – Summary and Conclusion

The high frequency termination family consists of two products – CT0404ALNWB1 (DC – 42.5 GHz, 5 W, termination) and CT0404ALN2WB1 (DC – 64 GHz, 1 W termination). Samples of both terminations above have been electrically and thermally tested; the test results presented in this test report are evidence of the performance that meets the required specifications.

A rigorous qualification testing as per TP-9270 has also been performed on a 25-piece inspection lot of the CT0404ALN1WB1 design. The test consisted of Group A, Group B, and Group C testing; the devices were subjected to thermal shock, burn in test, RF test over temperature, low temperature operation test, peak power and power conditioning test, high temperature exposure test, wire bond integrity test, solder mount integrity test, and life test. The results of these qualification test have been presented in this report. As shown, the inspection lot passed all the specifications as required by the TP-9270 and corresponding SCD. It has therefore been determined that the product **CT0404ALN1WB1 is qualified to be released into a full production**.

The product CT0404ALN2WB1 has been characterized by the identical bill of materials and processing router as the previously qualified product CT0404ALN1WB1. In other words, both products of interest share the identical constitutive material list and identical set of processing steps used to make them. The only difference is in geometrical shapes of the metalized and resistive features on the front surface of the ceramic substrate. Figure 35 shows the internal mechanical layout of both products. By similarity with CT0404ALN1WB1, it is determined that **CT0404ALN2WB1 is qualified to be released into a full production**.



